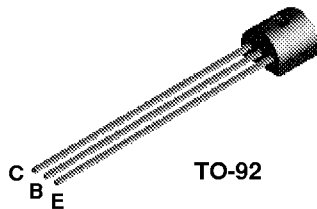


MPSA18



NPN General Purpose Amplifier

This device is designed for low noise, high gain, applications at collector currents from 1 μ A to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	6.5	V
I _C	Collector Current - Continuous	100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MPSA18	
P _D	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

NPN General Purpose Amplifier

(continued)

MPSA18

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	45		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	45		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	6.5		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		50	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_C = 10 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$	400 500 500 500	1500	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.2 0.3	V V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$		0.7	V

SMALL SIGNAL CHARACTERISTICS

C_{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$		3.0	pF
C_{eb}	Emitter-Base Capacitance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$		6.5	pF
f_T	Current Gain - Bandwidth Product	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$	100		MHz
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A},$ $R_S = 10 \text{ k}\Omega, f = 1.0 \text{ kHz},$		1.5	dB

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$